**Product data sheet** 

## 1. General description

High voltage, high speed, planar passivated NPN power switching transistor with integrated antiparallel E-C diode in a SOT428 (DPAK) surface-mountable plastic package.

## 2. Features and benefits

- Fast switching
- High voltage capability
- · Integrated anti-parallel E-C diode
- Surface mountable package
- Very low switching and conduction losses

## 3. Applications

- DC-to-DC converters
- Electronic lighting ballasts
- Inverters
- Motor control systems

## 4. Pinning information

#### **Table 1. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	[]	Ç
2	С	collector[1]		_
3	Е	emitter		В
mb	С	mounting base; connected to collector		 E sym131
			DPAK (SOT428)	

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package

### NPN power transistor with integrated diode

# 5. Ordering information

#### **Table 2. Ordering information**

Type number	Package				
	Name	Description	Version		
BUJD203AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

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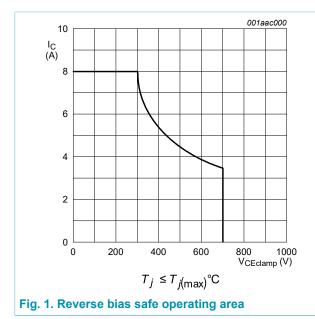
#### NPN power transistor with integrated diode

## 6. Limiting values

#### **Table 3. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	850	V
$V_{CBO}$	collector-base voltage	I <sub>E</sub> = 0 A	-	850	V
$V_{CEO}$	collector-emitter voltage	I <sub>B</sub> = 0 A	-	425	V
I <sub>C</sub>	collector current	DC; Fig. 1; Fig. 2; Fig. 3	-	4	Α
I <sub>CM</sub>	peak collector current	Fig. 1; Fig. 2; Fig. 3	-	8	Α
I <sub>B</sub>	base current	DC	-	2	Α
I <sub>BM</sub>	peak base current		-	4	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; <u>Fig. 4</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
T <sub>j</sub>	junction temperature		-	150	°C



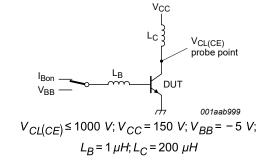
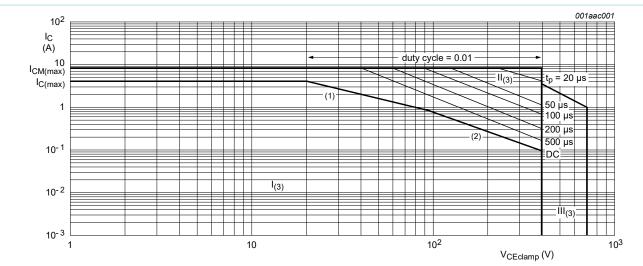


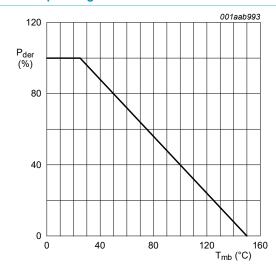
Fig. 2. Test circuit for reverse bias safe operating area

#### NPN power transistor with integrated diode



- 1)Ptot maximum and Ptot peak maximum lines
- 2)Second breakdown limits
- 3) I = Region of permissable DC operation
- II = Extension for repetitive pulse operation
- III = Extension during turn-on in single transistor converters provided that RBE  $\leq$  100  $\Omega$  and tp  $\leq$  0.6  $\mu$ s

Fig. 3. Forward bias safe operating area for Tmb ≤ 25 °C



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig. 4. Normalized total power dissipation as a function of mounting base temperature

#### NPN power transistor with integrated diode

### 7. Thermal characteristics

**Table 4. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint; Fig. 6	-	75	-	K/W

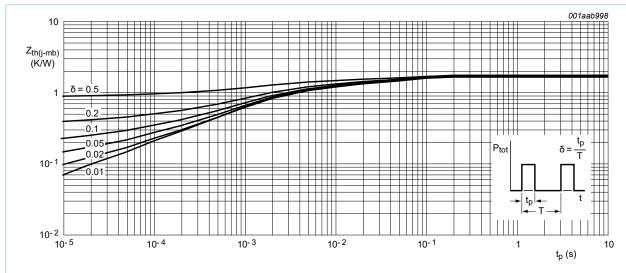


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

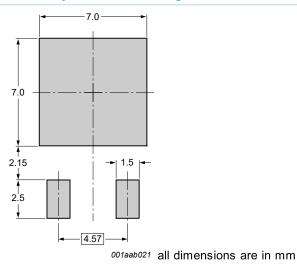


Fig. 6. Minimum footprint SOT428

### NPN power transistor with integrated diode

### 8. Characteristics

#### Table 5. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
I <sub>CES</sub>	collector-emitter cut-off	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 850 V; T <sub>j</sub> = 125 °C	[1]	-	-	2	mA
	current (base shorted)	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 850 V; T <sub>j</sub> = 25 °C	[1]	-	-	1	mA
I <sub>CBO</sub>	collector-base cut-off current (emitter open)	$V_{CB} = 850 \text{ V}; I_{E} = 0 \text{ A}$	[1]	-	-	1	mA
I <sub>CEO</sub>	collector-emitter cut-off current (base open)	$V_{CE} = 425 \text{ V}; I_B = 0 \text{ A}$	[1]	-	-	0.1	mA
I <sub>EBO</sub>	emitter-base cut-off current (collector open)	$V_{EB} = 7 \text{ V}; I_{C} = 0 \text{ A}$		-	-	10	mA
$V_{CEOsus}$	collector-emitter sustaining voltage (base open)	I <sub>B</sub> = 0 A; I <sub>C</sub> = 10 mA; L <sub>C</sub> = 25 mH; <u>Fig. 7</u> ; <u>Fig. 8</u>		400	450	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 3 A; I <sub>B</sub> = 0.6 A; <u>Fig. 9</u> ; <u>Fig. 10</u>		-	0.29	1	V
$V_{BEsat}$	base-emitter saturation voltage	I <sub>C</sub> = 3 A; I <sub>B</sub> = 0.6 A; <u>Fig. 11</u>		-	0.99	1.5	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 2 A; T <sub>j</sub> = 25 °C		-	1.04	1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 1 \text{ mA}$ ; $V_{CE} = 5 \text{ V}$ ; $T_{mb} = 25 ^{\circ}\text{C}$ ; Fig. 12		10	15	32	
		$I_C$ = 500 mA; $V_{CE}$ = 5 V; $T_{mb}$ = 25 °C; Fig. 12		13	21	32	
		I <sub>C</sub> = 2 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; Fig. 12		11	16	22	
		I <sub>C</sub> = 3 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; Fig. 12		-	12.5	-	
Dynamic cl	naracteristics						
t <sub>on</sub>	turn-on time	$I_C = 2.5 \text{ A}$ ; $I_{Bon} = 0.5 \text{ A}$ ; $I_{Boff} = -0.5 \text{ A}$ ;		-	0.52	0.6	μs
t <sub>s</sub>	storage time	$R_L = 75 \Omega$ ; $T_j = 25 ^{\circ}C$ ; resistive load; Fig. 13; Fig. 14		-	2.7	3.3	μs
		$I_C$ = 2 A; $I_{Bon}$ = 0.4 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_j$ = 25 °C; inductive load; <u>Fig. 15</u> ; <u>Fig. 16</u>		-	1.2	1.4	μs
		$I_C$ = 2 A; $I_{Bon}$ = 0.4 A; $V_{BB}$ = -5 V; $L_B$ = 1 $\mu$ H; $T_j$ = 100 °C; inductive load; Fig. 15; Fig. 16		-	-	1.8	μs
t <sub>f</sub>	fall time	$I_C$ = 2.5 A; $I_{Bon}$ = 0.5 A; $I_{Boff}$ = -0.5 A; $R_L$ = 75 $\Omega$ ; resistive load; Fig. 13; Fig. 14		-	0.3	0.35	μs
		I <sub>C</sub> = 2 A; I <sub>Bon</sub> = 0.4 A; V <sub>BB</sub> = -5 V;		-	-	0.12	μs
		L <sub>B</sub> = 1 μH; inductive load; <u>Fig. 15;</u> <u>Fig. 16</u>		-	0.03	0.06	μs
		I					

[1] Measured with half-sine wave voltage (curve tracer)

#### NPN power transistor with integrated diode

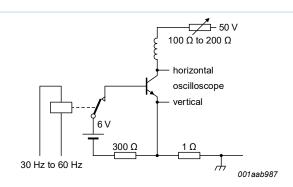


Fig. 7. Test circuit for collector-emitter sustaining voltage

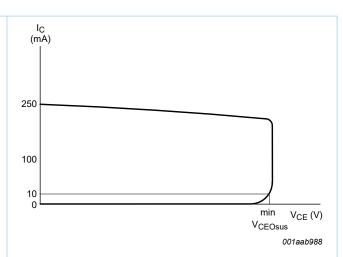


Fig. 8. Oscilloscope display for collector-emitter sustaining voltage test waveform

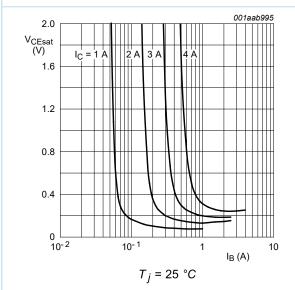


Fig. 9. Collector-emitter saturation voltage as a function of base current; typical values

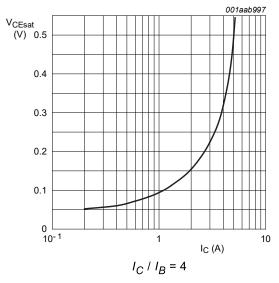


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

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#### NPN power transistor with integrated diode

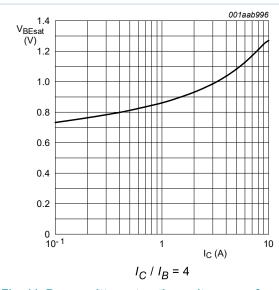


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

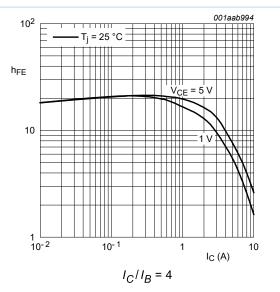
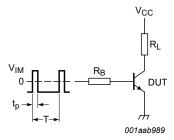


Fig. 12. DC current gain as a function of collector current; typical values



 $V_{IM}$  = -6 to +8 V;  $V_{CC}$  = 250 V;  $t_p$  = 20  $\mu$ s;  $\delta$  =  $\frac{t_p}{T}$  = 0.01  $R_B$  and  $R_L$  calculated from  $I_{Con}$  and  $I_{Bon}$  requirements.

Fig. 13. Test circuit for resistive load switching

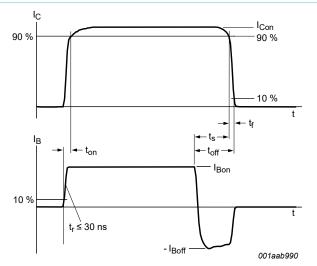
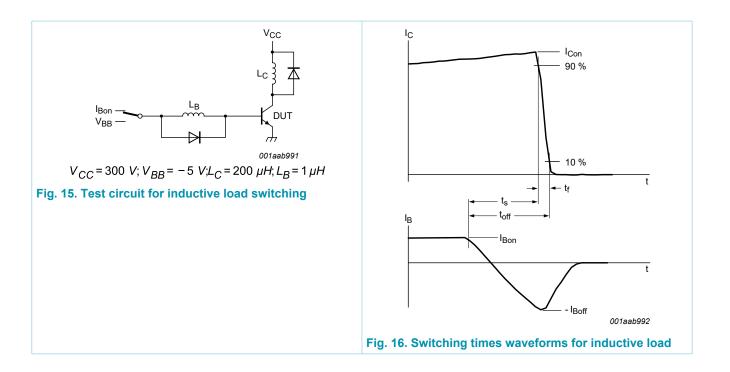


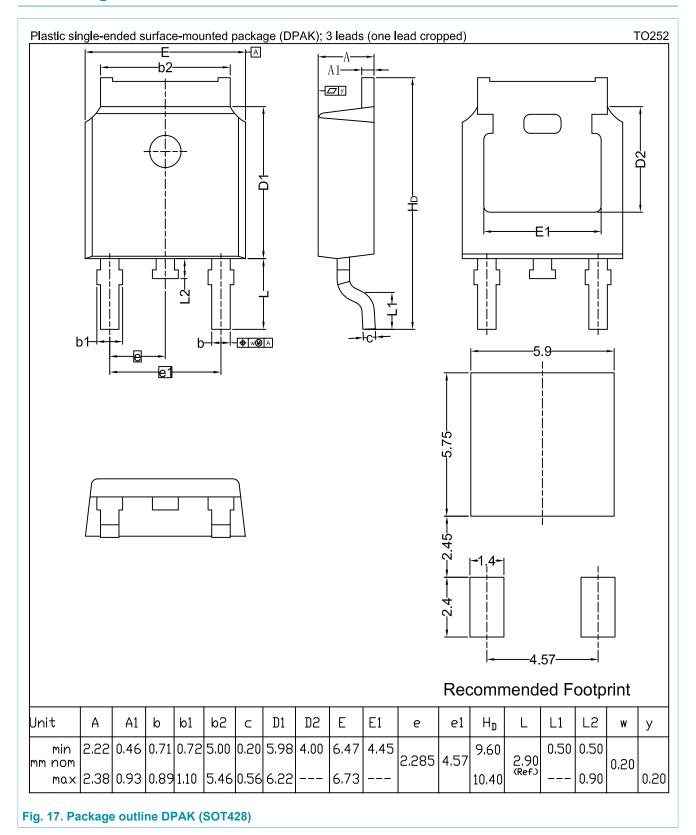
Fig. 14. Switching times waveforms for resistive load

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## 9. Package outline



#### NPN power transistor with integrated diode

# 10. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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#### NPN power transistor with integrated diode

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### NPN power transistor with integrated diode

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For more information, please visit: http://www.ween-semi.com
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